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| Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: June 14, 2005 <i>(use as many sheets as necessary)</i> | | | | Complete if Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%;">Application Number</td> <td style="width: 50%;">Unassigned 10/538739</td> </tr> <tr> <td>Filing Date</td> <td>6/14/2005</td> </tr> <tr> <td>First Named Inventor</td> <td>Yasuhiro OKAMOTO</td> </tr> <tr> <td>Group Art Unit</td> <td>Unassigned</td> </tr> <tr> <td>Examiner Name</td> <td>Unassigned</td> </tr> <tr> <td>Attorney Docket Number</td> <td>029437-0108</td> </tr> </table> | | Application Number | Unassigned 10/538739 | Filing Date | 6/14/2005 | First Named Inventor | Yasuhiro OKAMOTO | Group Art Unit | Unassigned | Examiner Name | Unassigned | Attorney Docket Number | 029437-0108 |
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| First Named Inventor | Yasuhiro OKAMOTO | | | | | | | | | | | | | | | | |
| Group Art Unit | Unassigned | | | | | | | | | | | | | | | | |
| Examiner Name | Unassigned | | | | | | | | | | | | | | | | |
| Attorney Docket Number | 029437-0108 | | | | | | | | | | | | | | | | |
| Sheet | 1 | of | 1 | | | | | | | | | | | | | | |

U.S. PATENT DOCUMENTS

| Examiner Initials* | Cite No. ¹ | U.S. Patent Document | | Name of Patentee or Applicant of Cited Document | Date of Publication of Cited Document MM-DD-YYYY | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
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| | | Number | Kind Code ² (if known) | | | |
| | A1 | 2002-0005528 | A1 | Masaki NAGAHARA | 01/17/2002 | |
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| Examiner Initials* | Cite No. ¹ | Foreign Patent Document | | | Name of Patentee or Applicant of Cited Documents | Date of Publication of Cited Document MM-DD-YYYY | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | T ⁶ |
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| | | Office ³ | Number ⁴ | Kind Code ⁵ (if known) | | | | |
| | A2 | JP | 09-307097 | A | Sony Corp. | 11/28/1997 | | A |
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| Examiner Initials* | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published. | T ⁶ |
|--------------------|-----------------------|--|----------------|
| | A7 | ANDO et al., "A 110-W AlGaIn/GaN Heterojunction FET on Thinned Sapphire Substrate," IEDM 01, 2001, pp. 381-384. | |
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| | A10 | TAN et al., "The Effect of Dielectric Stress on the Electrical Characteristics of AlGaIn/GaN Heterostructure Field-Effect Transistors (HFETs)," The 10 th IEEE International Symposium on Electron Devices for Microwave and Optoelectronic Applications, November 2002, pp. 130-135. | |
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| Examiner Signature | /Sarah Salerno/ | Date Considered | /S.K.S./ |
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